

- # Methoden moderner Röntgenphysik II: Streuung und Abbildung

Lecture 4

Vorlesung zum Haupt/Masterstudiengang Physik

SS 2014

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Location: Hörs AP, Physik, Jungiusstrasse

Tuesdays 12.45 – 14.15

Thursdays 8:30 – 10.00

■ Methoden moderner Röntgenphysik II: Streuung und Abbildung

Introduction

Overview, Introduction to X-ray scattering

X-ray Scattering Primer

Elements of X-ray scattering

Sources of X-rays, Synchrotron Radiation
accelerator bases sources

Laboratory sources,

Reflection and Refraction

Snell's law, Fresnel equations,

Kinematical Diffraction (I)

Diffraction from an atom, molecule, liquids, glasses,..

Kinematical Diffraction (II)

Diffraction from a crystal, reciprocal lattice, structure factor,..

- **Methoden moderner Röntgenphysik II:
Streuung und Abbildung**

Small Angle Scattering, and Soft Matter

Introduction, form factor, structure factor, applications, ..

Anomalous Diffraction

Introduction into anomalous scattering,..

Introduction into Coherence

Concept, First order coherence, ..

Coherent Scattering

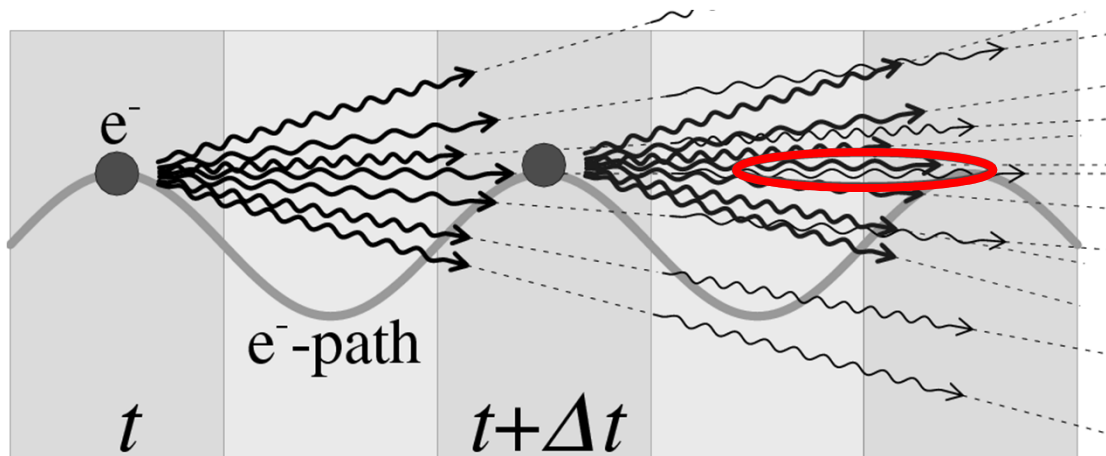
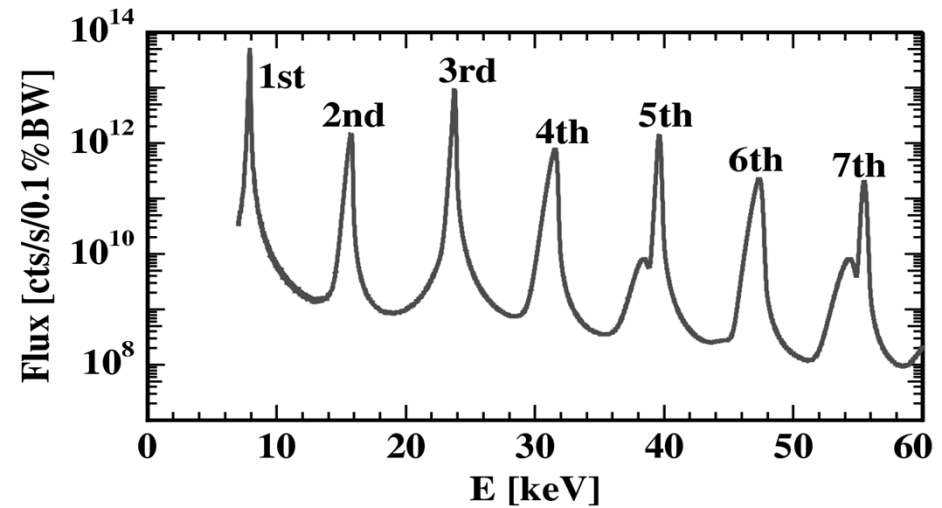
Spatial coherence, second order coherence,..

Applications of coherent Scattering

Imaging and Correlation spectroscopy,..

Undulator spectrum

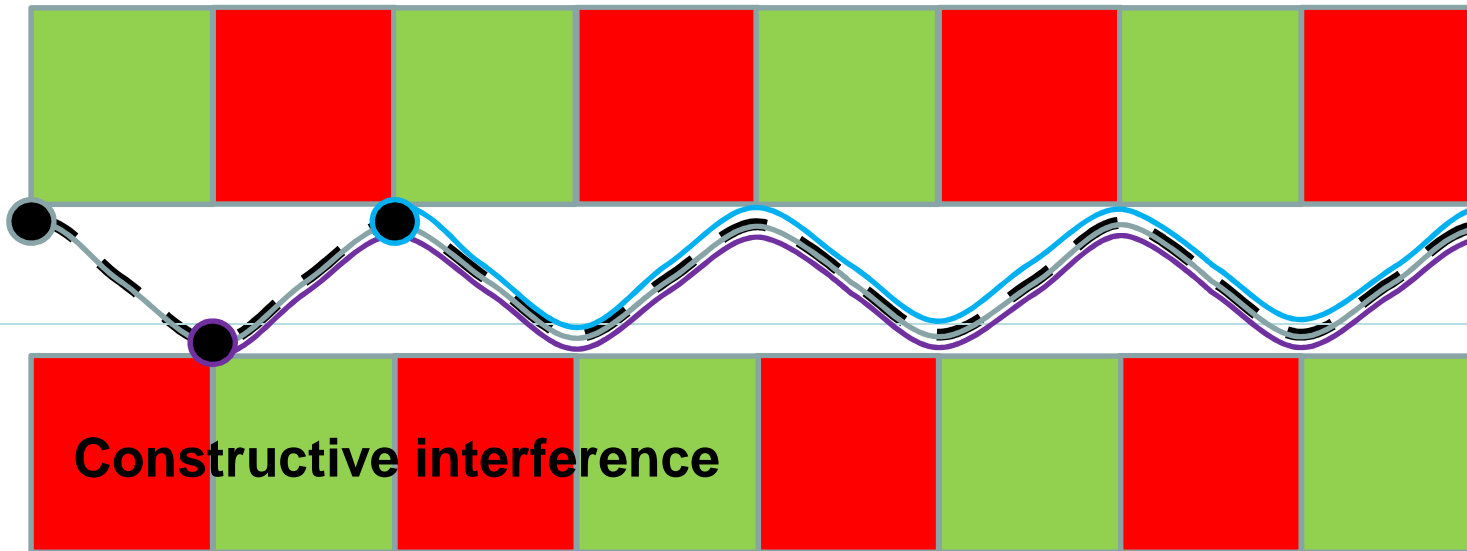
At some photon energies resonance appears and the flux is high



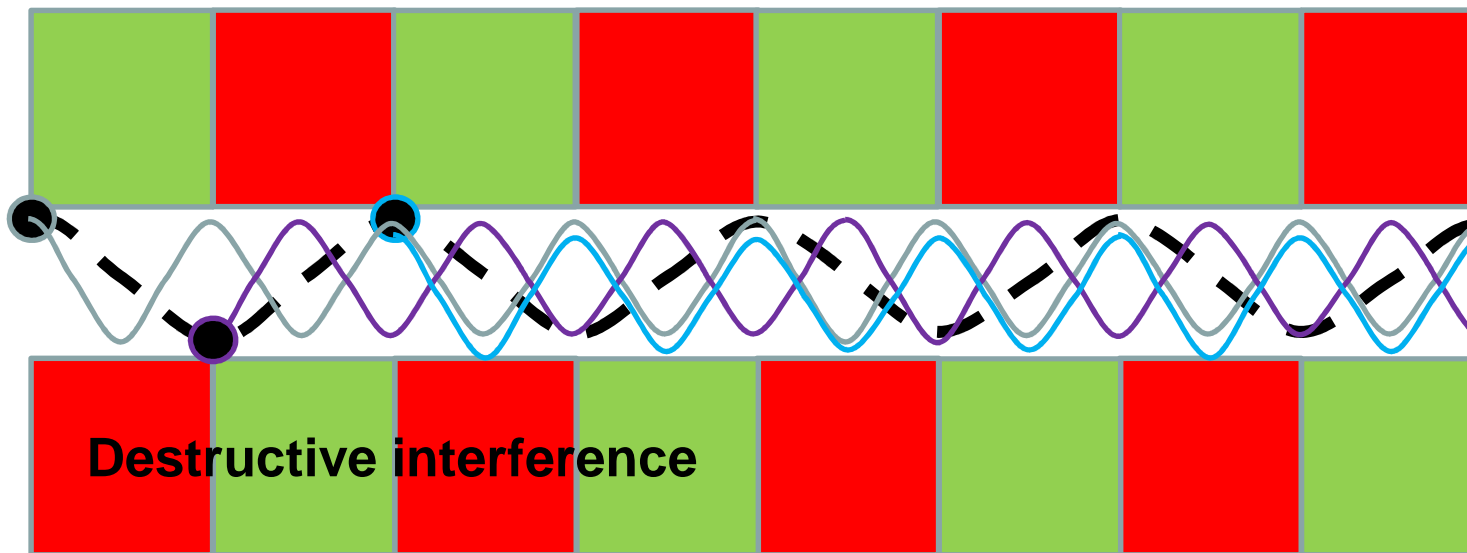
In **forward direction** some particular waves can interfere with the wave emitted from the **same electron** one magnetic bend before!!

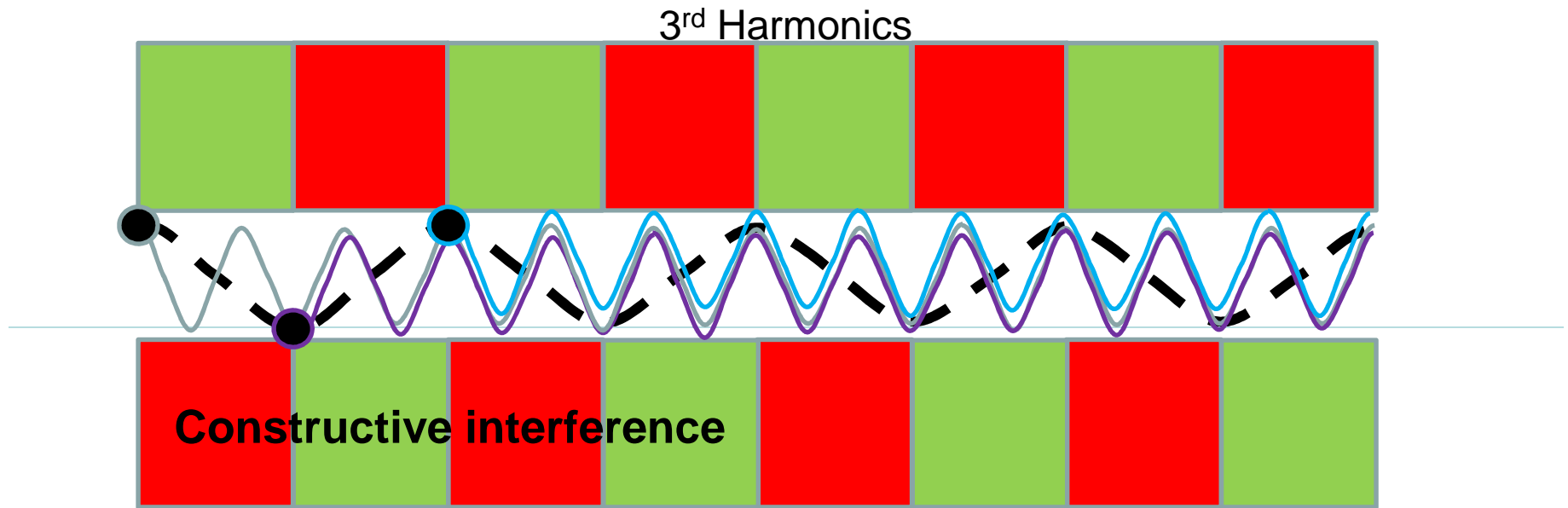
The odd harmonics have higher flux than the even harmonics but the even harmonics are not zero

Fundamental = 1st Harmonics



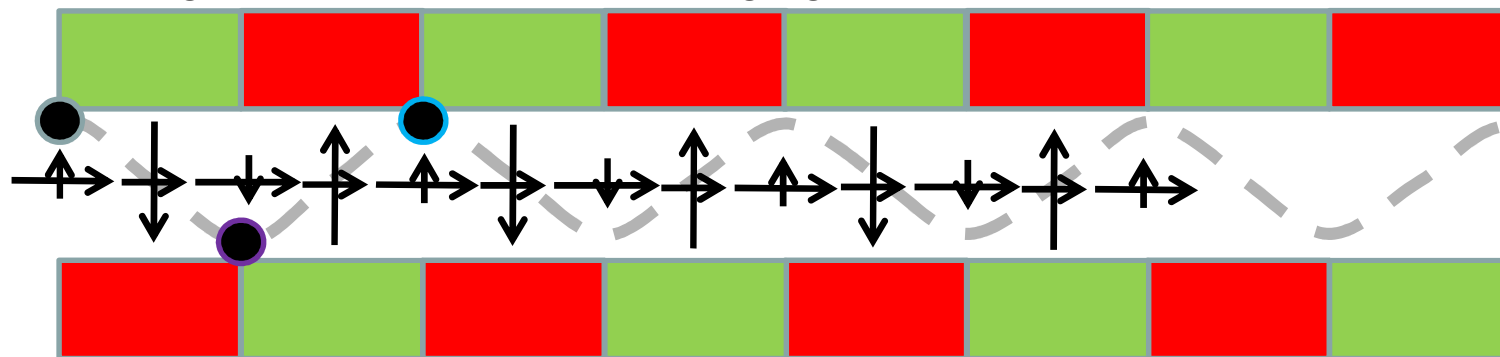
2nd Harmonics





Why are there 2nd Harmonics at all ???

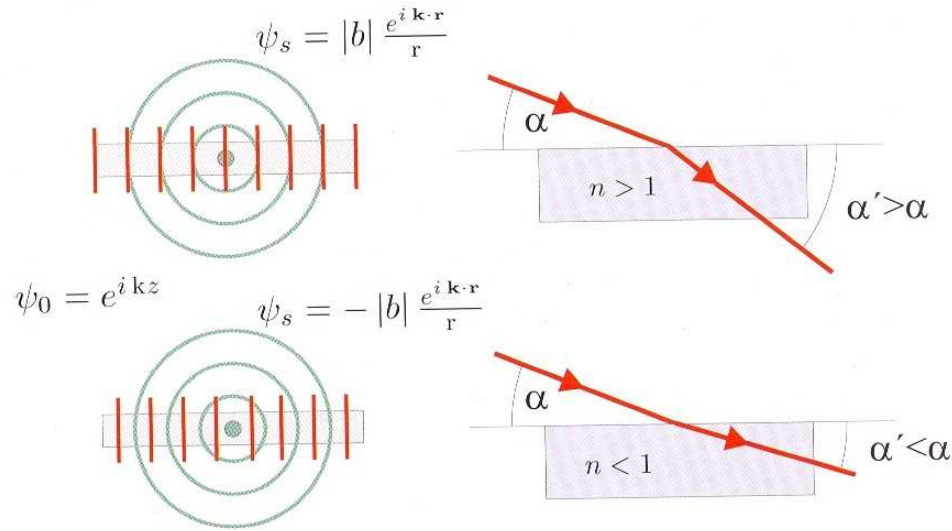
Electrons are strongly relativistic and cannot be accelerated by magnetic field to values larger than c . Magnetic field introduces a speed component perpendicular to travel direction. Therefore, the speed component along the magnet structure is also changing => even harmonics allowed !!!!!



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Refraction and Reflexion from Interfaces

Refraction and Reflexion from Interfaces



Rays of light propagating in air change direction when entering glass, water or another transparent material.

Governed by Snell's law:

$$\cos\alpha / \cos\alpha' = n \text{ (refractive index)}$$

$$n = n(\omega) \quad 1.2 < n < 2 \text{ visible light}$$

$$n < 1 \text{ X-rays } (\alpha' < \alpha)$$

$$n = 1 - \delta \quad \delta \approx 10^{-5}$$

Note: spherical wave $\exp(i\mathbf{k}\cdot\mathbf{r})$

$$k' = nk = (n/c)\omega = \omega/v$$

with $v=c/n$ phase velocity

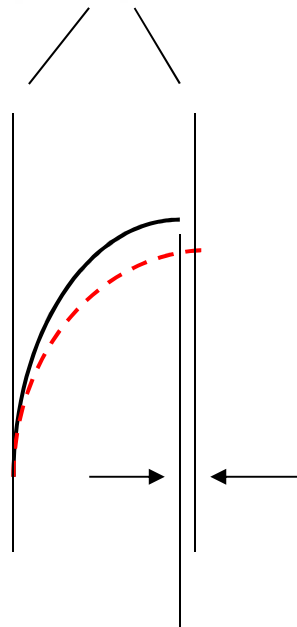
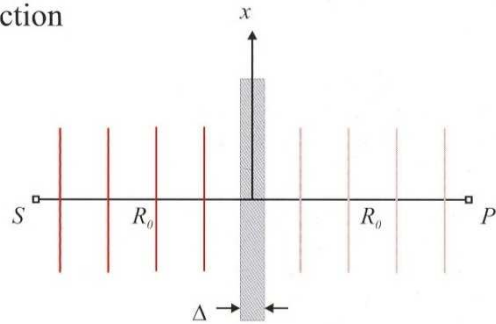
($v > c$ for $n < 1$; but group velocity $d\omega/dk \leq c$)

total external reflexion:

for $\alpha < \alpha_c$ (critical angle)

Refractive Index

Refraction



Phase difference

Refractive picture:

Consider plane wave impinging on a slab with thickness Δ and refractive index n . Evaluate amplitude at observation point P (compared to the situation without slab).

$$\left. \begin{array}{l} \text{no slab: } \exp(ik\Delta) \\ \text{slab: } \exp(ink\Delta) \end{array} \right\} \begin{array}{l} \text{phase difference:} \\ \exp(i(nk-k)\Delta) \end{array}$$

amplitude:

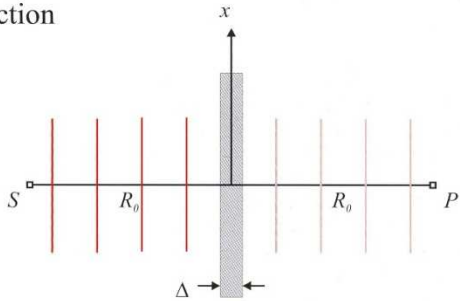
$$\begin{aligned} \Psi_{\text{tot}}^P / \Psi_0^P &= \exp(ink\Delta) / \exp(ik\Delta) \\ &= \exp(i(nk-k)\Delta) \end{aligned}$$

$$\exp(i\alpha) = \cos\alpha + i\sin\alpha \xrightarrow{\alpha \text{ small}} 1+i\alpha$$

$$\Psi_{\text{tot}}^P \approx \Psi_0^P [1 + i(n-1)k\Delta] \quad (\$)$$

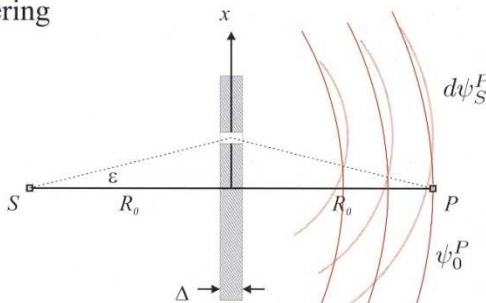
Refractive Index

Refraction



$$\psi_{tot}^P = \psi_0^P e^{i(nk-k)\Delta} \approx \psi_0^P [1 + i(n-1)k\Delta]$$

Scattering



$$\phi(x, y) = k(2R - 2R_0) \approx k(x^2 + y^2)/R_0$$

- $d\psi_S^P = \left(\frac{e^{ikR_0}}{R_0}\right)$ incident wave
- $(\rho \Delta dx dy)$ number of scatterers
- $\left(-b \frac{e^{ikR_0}}{R_0}\right)$ spherical wave from one scatterer
- $e^{i\phi(x,y)}$ apart from this phase factor

$$\psi_{tot}^P = \psi_0^P + \int d\psi_S^P = \psi_0^P \left[1 - i \frac{2\pi \rho b \Delta}{k}\right]$$

Scattering picture:

$$R = \sqrt{R_0^2 + x^2} = \sqrt{R_0^2(1 + x^2/R_0^2)}$$

$$\approx R_0 \sqrt{1 + x^2/R_0^2 + x^4/4R_0^4}$$

$$= R_0 \sqrt{\{1 + x^2/2R_0^2\}^2} = R_0 [1 + x^2/2R_0^2]$$

phase difference (2kR) btw. direct rays and rays following path R;

$$2kx^2/2R_0 = kx^2/R_0$$

include y direction:

$$\exp(i\Phi(x,y)) = \exp(i(x^2 + y^2)k/R_0)$$

amplitude at P:

$$d\psi_S^P \approx$$

$$\exp(ikR_0)/R_0 \quad (\rho \Delta dx dy) \quad (b \exp(ikR_0)/R_0) \quad \exp(i\Phi(x,y))$$

incident wave

number of scatters
in volume element
 $\rho dx dy$

scattered wave
from 1 scatterer

phase factor

Refractive Index

$$\Psi_S^P = \int d\Psi_S^P = -\rho b \Delta \{ \exp(i2kR_0) \} / R_0^2 \bullet \frac{\int \exp(i\Phi(x,y)) dx dy}{i\pi R_0 / k} \quad [1]$$

↑
[Ref. 1]

Amplitude at P without slab:

$$\Psi_o^P = \{ \exp(ik2R_0) \} / 2R_0 \quad [2]$$

$$\Psi_{tot}^P = [1] + [2] = \Psi_o^P [1 - i2\pi\rho b \Delta / k] \equiv (\$) \equiv \Psi_o^P [1 + i(n-1)k\Delta]$$

$$\rightarrow n = 1 - 2\pi\rho b / k^2 = 1 - \delta$$

If a homogeneous electron density ρ is replaced by a plate composed of atoms:

$$\rho = \rho_a f^0(0)$$

Number density x atomic scattering factor

$$\delta = 2\pi\rho_a f^0(0) r_0 / k^2$$

Total external reflexion ($\alpha'=0$) for $\alpha = \alpha_c$:

$$\cos\alpha = n \cos\alpha'$$

$$\cos\alpha_c = 1 - \delta = 1 - \alpha_c^2 / 2$$

$$\alpha_c = \text{sqrt}(2\delta) = \text{sqrt}(4\pi\rho r_0 / k^2)$$

$$k = 2\pi/\lambda = 4\text{\AA}^{-1}, \quad b = r_0 = 2.82 \times 10^{-5} \text{\AA}, \quad \rho = 1 \text{e}^- / \text{\AA}^3: \quad \delta \approx 10^{-5}$$

[Ref. 1: Als-Nielsen & McMorrow p.66]

- critical angle for Si

$$\alpha_c = \sqrt{2\delta} = \sqrt{4\pi\rho r_0/k^2}$$

Silicon: $\rho = 0.699 \text{ e}/\text{\AA}^3$, $\lambda = 1 \text{ \AA}$

$$\alpha_c = \sqrt{4\pi \times 0.699 \times 2.82 \times 10^{-5} \times 1/(2\pi)^2}$$

$$= 0.0025 \text{ rad}$$

$$Q_c = (4\pi/\lambda) \sin\alpha_c = 0.032 \text{ \AA}^{-1}$$

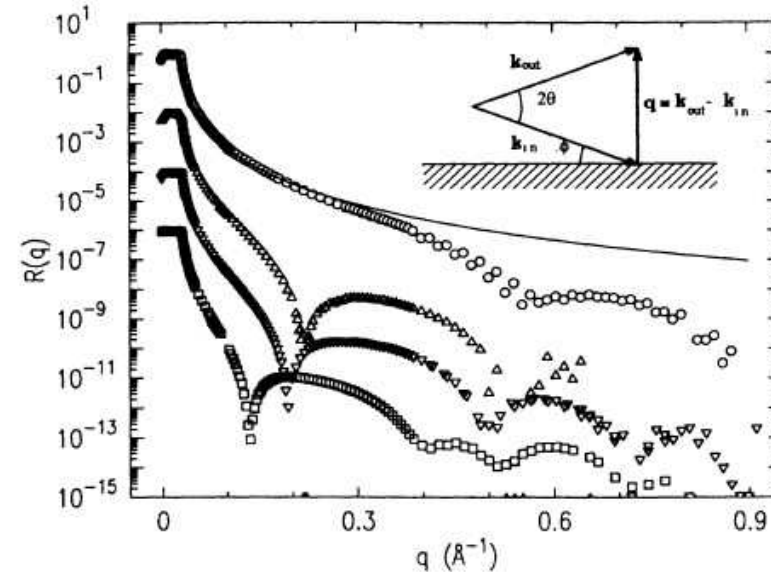
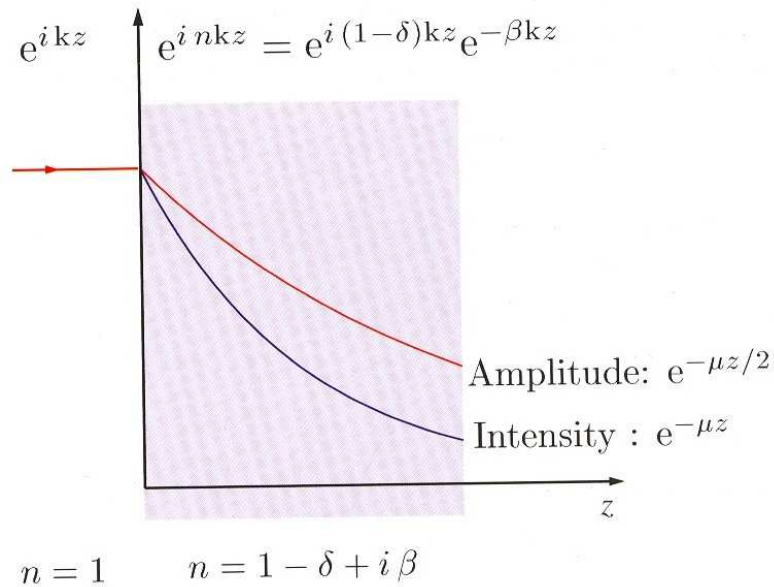


FIG. 1. Normalized reflectivity data from several samples. Successive data sets are displaced by 100 times and error bars omitted for clarity. (—) Theoretical reflectivity from an ideal step interface with bulk silicon density. (○) Uncoated silicon sample in helium; the “pairing” of points occurs for two scans taken 60 min apart and is probably due to the build up of contaminants on the surface. (△) 10-carbon chain alkylsiloxane. (▽) 12-carbon chain alkylsiloxane. (□) 18-carbon chain alkylsiloxane. The inset shows a schematic diagram of the scattering vectors for the specular reflectivity condition, where $2(\phi) = 2\theta$.

▪ Refraction including absorption



$$n = 1 - \delta + i\beta$$

wave propagating in a medium:

$$\exp(inkz) = \exp(i(1-\delta)kz) \exp(-\beta kz)$$

attenuation of amplitude: $\exp(-\mu z/2)$

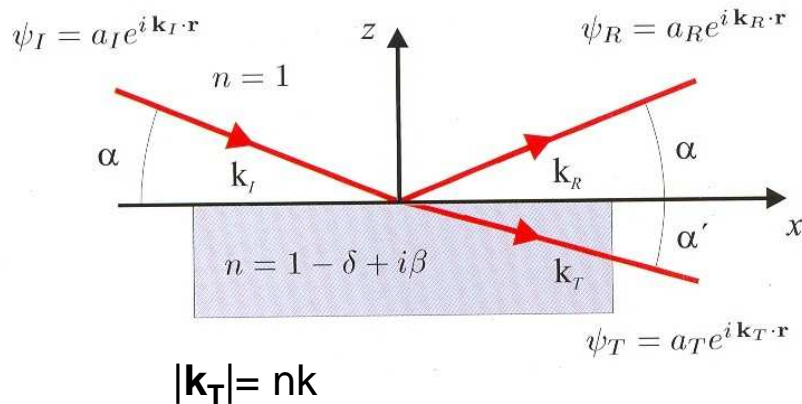
(when intensity drops according to $\exp(-\mu z)$)

$$\beta = \mu/2k$$

- # Snell's law and the Fresnel equations

Snell's law and the Fresnel equations

$$k = |\mathbf{k}_I| = |\mathbf{k}_R|$$



$$|\mathbf{k}_T| = nk$$

Require that the wave and its derivative is continuous at the interface:

$$a_I + a_R = a_T \quad (A)$$

$$a_I \mathbf{k}_I + a_R \mathbf{k}_R = a_T \mathbf{k}_T \quad (B)$$

$$\parallel: a_I k \cos \alpha + a_R k \cos \alpha = a_T (nk) \cos \alpha' \quad (B')$$

$$\perp: -(a_I - a_R) k \sin \alpha = -a_T (nk) \sin \alpha' \quad (B'')$$

$$\boxed{\cos \alpha = n \cos \alpha'} \quad (B' + A)$$

α, α' small: ($\cos z = 1 - z^2/2$)

$$\begin{aligned} \alpha^2 &= \alpha'^2 + 2\delta - 2i\beta \\ &= \alpha'^2 + \alpha_c^2 - 2i\beta \end{aligned} \quad (C)$$

$$a_I - a_R / a_I + a_R = n(\sin \alpha' / \sin \alpha) \approx \alpha' / \alpha \quad (B'' + A)$$

Fresnel equations:

$$r = a_R / a_I = (\alpha - \alpha') / (\alpha + \alpha')$$

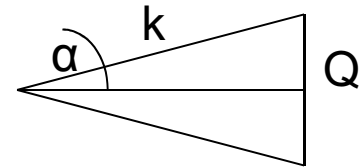
$$t = a_T / a_I = 2\alpha / (\alpha + \alpha')$$

r: reflectivity t: transmittivity

Snell's law and the Fresnel equations (2)

Note: α' is a complex number
 $\alpha' = \text{Re}(\alpha') + i \text{Im}(\alpha')$

use wavevector notation:



$$\sin \alpha = (Q/2)/k$$

Consider z-component of transmitted wave:

$$= a_T \exp(ik \sin \alpha' z) \approx a_T \exp(ik \alpha' z)$$

$$= a_T \exp(ik \text{Re}(\alpha') z) \bullet \exp(-k \text{Im}(\alpha') z)$$



exponential damping

intensity fall-off: $\exp(-2k \text{Im}(\alpha') z)$

$$Q \equiv 2k \sin \alpha \approx 2k \alpha$$

$$Q_c \equiv 2k \sin \alpha_c \approx 2k \alpha_c$$

use dimensionless units:

$$q \equiv Q/Q_c \approx (2k/Q_c) \alpha$$

$$q' \equiv Q'/Q_c \approx (2k/Q_c) \alpha'$$

1/e penetration depth Λ : $z \ 2k \text{Im}(\alpha') = 1 \quad (z = \Lambda)$

$$q^2 = q'^2 + 1 - 2 i b_u \tag{D}$$

$$\Lambda = 1 / 2k \text{Im}(\alpha')$$

$$b_u = (2k/Q_c) \beta = (4k^2/Q_c^2) \mu / 2k = 2k \mu / Q_c^2$$

$$Q_c = 2k \alpha_c = 2k \sqrt{2\delta}$$

▪ Snell's law and the Fresnel equations (3)

use table to extract μ , ρ , f' yielding Q_c

and calculate b_u ($b_u \ll 1$):

$$b_u = 2k\mu/Q_c^2$$

use (D): $q^2 = q'^2 + 1 - 2ib_u$

get:

$$r(q) = (q - q') / (q + q')$$

$$t(q) = 2q / (q + q')$$

$$\Lambda(q) = 1 / Q_c \operatorname{Im}(q')$$

	Z	Molar density (g/mole)	Mass density (g/cm ³)	ρ (e/Å ³)	Q_c (1/Å)	$\mu \times 10^6$ (1/Å)	b_μ
C	6	12.01	2.26	0.680	0.031	0.104	0.0009
Si	14	28.09	2.33	0.699	0.032	1.399	0.0115
Ge	32	72.59	5.32	1.412	0.045	3.752	0.0153
Ag	47	107.87	10.50	2.755	0.063	22.128	0.0462
W	74	183.85	19.30	4.678	0.081	33.235	0.0409
Au	79	196.97	19.32	4.666	0.081	40.108	0.0495

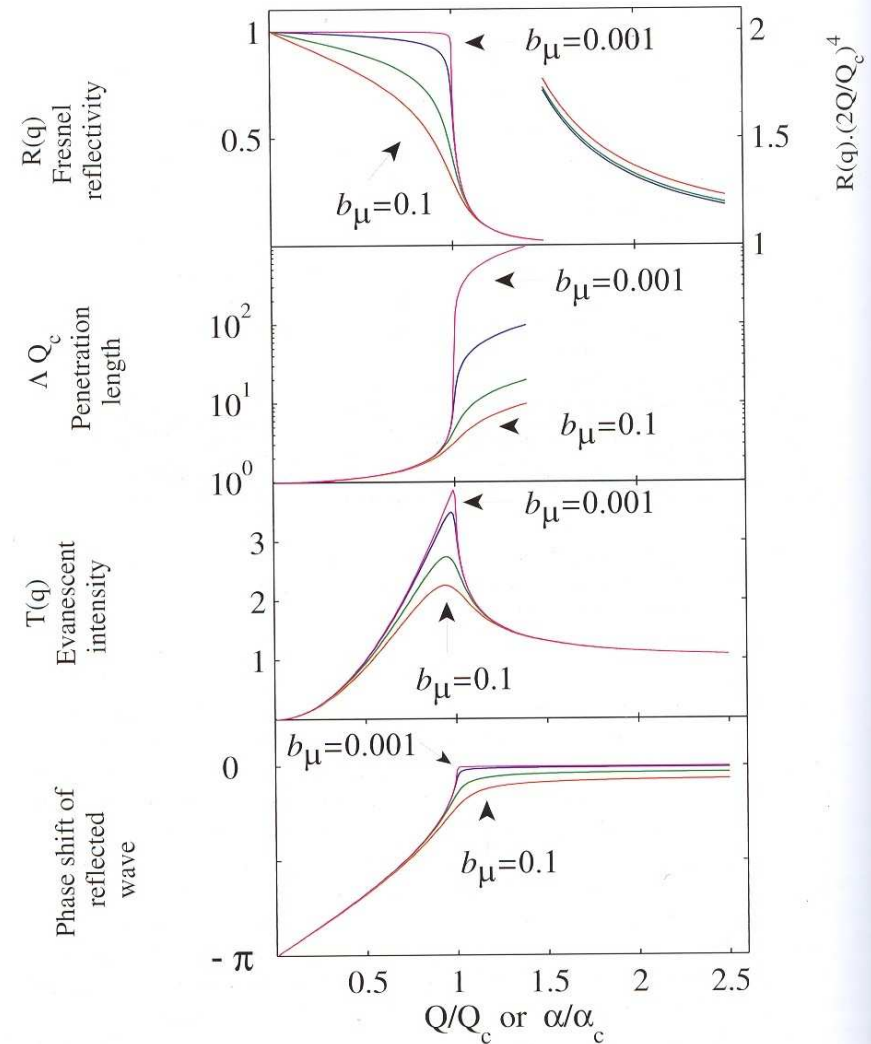
Snell's law and the Fresnel equations (4)

Fresnel equations:

$q \gg 1$: $R(Q) \sim 1/q^4$,
 $\Lambda \approx \mu^{-1}$,
 $T \approx 1$,
 no phase shift

$q \ll 1$: $R \approx 1$,
 $\Lambda \approx 1/q_c$ small,
 T very small,
 $-\pi$ phase shift

$q=1$: $T(q=1) \approx 4 a_1$



Examples

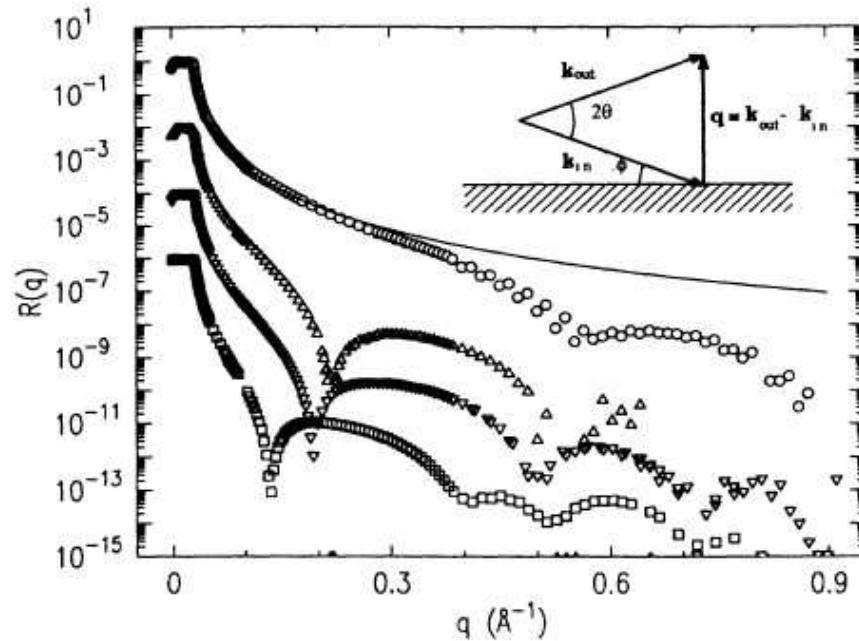


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PHYSICAL REVIEW B

VOLUME 41, NUMBER 2

15 JANUARY 1990-1

X-ray specular reflection studies of silicon coated by organic monolayers (alkylsiloxanes)

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(Received 3 October 1988; revised manuscript received 7 August 1989)

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